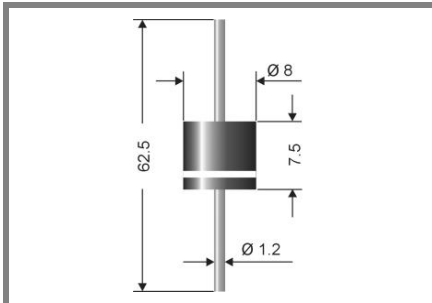


SBH 1820 ... SBH 1845



Axial lead diode

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
	V_{RRM} V	V_{RSM} V	$I_F = - A$ $I_R = - A$ $I_{RR} = - A$ t_{rr} ns	$V_F^{(2)}$
SBH 1820	20	20	-	0,46
SBH 1830	30	30	-	0,46
SBH 1840	40	40	-	0,46
SBH 1845	45	45	-	0,46

High temperature schottky barrier diodes

SBH1820 ... SBH1845

Forward Current: 18 A

Reverse Voltage: 20 to 45 V

Preliminary Data

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

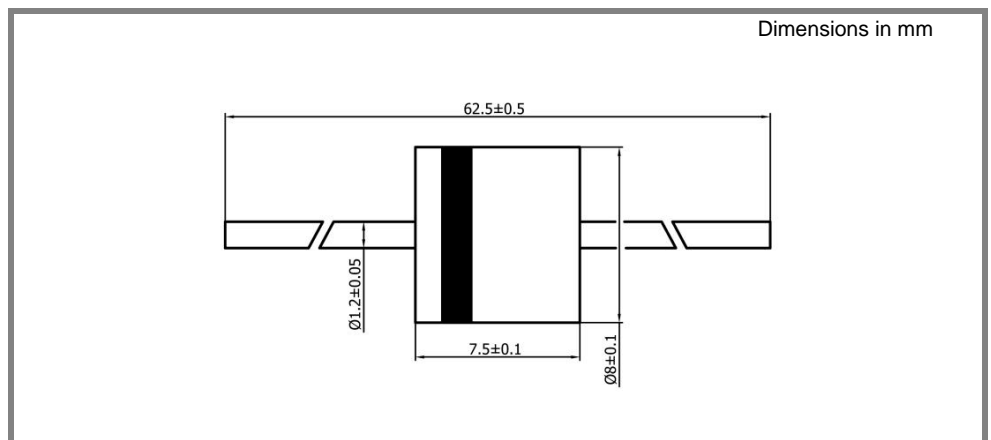
Mechanical Data

- Plastic case: 8 x 7,5 [mm]
- Weight approx.: 1,5 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per ammo or 1 000 pieces per reel

- 1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from case
- 2) $I_F = 5 A$, $V_F @ 18A < 0,56 V$, $T_J = 25 ^\circ C$
- 3) $T_A = 25 ^\circ C$
- 4) Thermal resistance from junction to lead/terminal at a distance 0 mm from case
- 5) Max. junction temperature $T_J \leq 200 ^\circ C$ in reverse mode $V_R = 50\% V_{RRM}$ and in bypass mode / DC forward mode

Absolute Maximum Ratings		$T_A = 25 ^\circ C$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 50 ^\circ C$ ¹⁾	18	A
I_{FRM}	Repetitive peak forward current $f > 15 Hz$ ¹⁾	70	A
I_{FSM}	Peak forward surge current 10 Hz half sinus-wave ³⁾	600	A
i^2t	Rating for fusing, $t < 10 ms$ ³⁾	1800	A ² s
R_{thA}	Max. thermal resistance junction to ambient ¹⁾		K/W
R_{thL}	Max. thermal resistance junction to terminals ⁴⁾	2,5	K/W
T_j	Operating junction temperature	- 50 ... + 185 ($T_j \leq 200 ^\circ C$ in reverse mode $V_R = 50\% V_{RRM}$ ⁵⁾)	$^\circ C$
T_s	Storage temperature	- 50 ... + 175	$^\circ C$

Characteristics		$T_A = 25 ^\circ C$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25 ^\circ C$; $V_R = V_{RRM}$	< 75	μA
	$T_j = ^\circ C$; $V_R = V_{RRM}$		
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_j = ^\circ C$; inductive load switched off)	-	mJ



case: 7,5 x 8 [mm]

